

PDTB123ET

PNP 500 mA, 50 V resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

Rev. 3 — 22 September 2010

Product data sheet

1. Product profile

1.1 General description

500 mA PNP Resistor-Equipped Transistor (RET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTD123ET.

1.2 Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- ±10 % resistor ratio tolerance
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC807 series in digital applications
- Switching loads

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-500	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	



PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

2. Pinning information

Table 2. Pinning

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Pin	Description	Simplified outline	Graphic symbol
1	input (base)		
2	GND (emitter)	3	3
3	output (collector)	1 2 006aaa144	1 R1 R2 2
		000ada144	sym003

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PDTB123ET	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PDTB123ET	*7\$

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
V_{I}	input voltage				
	positive		-	+10	V
	negative		-	-12	V
Io	output current		-	-500	mA

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	500	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

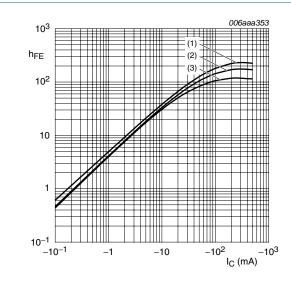
7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base	$V_{CB} = -40 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
	cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; I_B = 0 \text{ A}$	-	-	-0.5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-2.0	mA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V};$ $I_{C} = -50 \text{ mA}$	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -50 \text{ mA};$ $I_B = -2.5 \text{ mA}$	-	-	-0.3	V
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$	-0.6	-1.1	-1.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_{C} = -20 \text{ mA}$	-1.0	-1.5	-2.0	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.9	1.0	1.1	
C _c	collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A};$ f = 100 MHz	-	11	-	pF

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

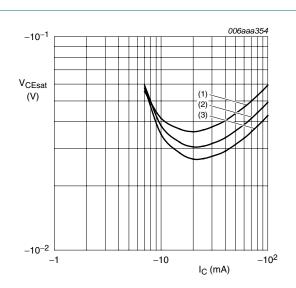


$$V_{CE} = -5 \text{ V}$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values



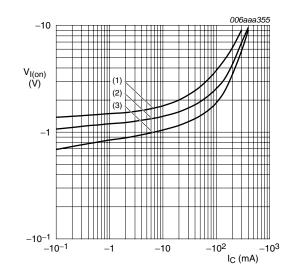
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. Collector-emitter saturation voltage as a function of collector current; typical values



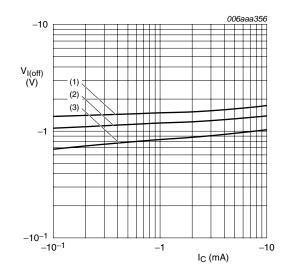
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 3. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 4. Off-state input voltage as a function of collector current; typical values

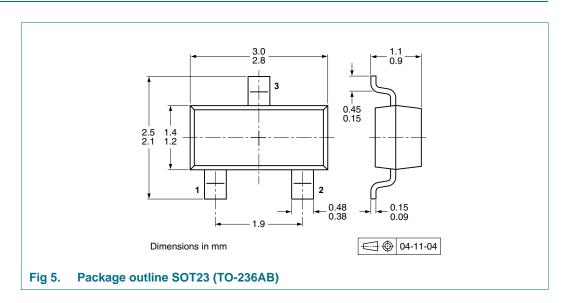
PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

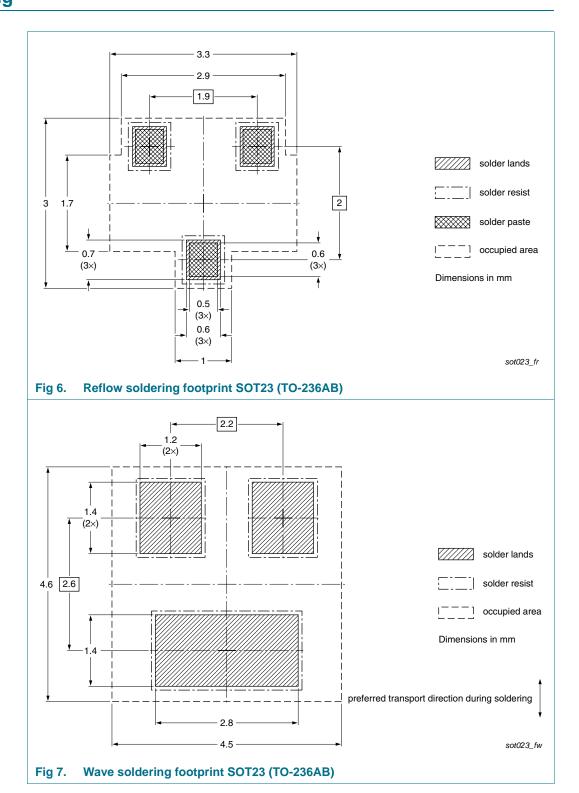
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Pac	cking qu	antity
			300	00	10000
PDTB123ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	5	-235

^[1] For further information and the availability of packing methods, see Section 14.

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

11. Soldering



PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTB123ET v.3	20100922	Product data sheet	-	PDTB123E_SER_2
Modifications:	 Type numbers I 	PDTB123EK and PDTB123	BES deleted.	
	• Table 7 "Charac	cteristics": unit for V _{CEsat} ch	anged from mV to V.	
	 Section 8 "Test 	information": added.		
	 Section 11 "Sole 	dering": added.		
	 Section 13 "Leg 	<u>gal information"</u> : updated.		
PDTB123E_SER_2	20091116	Product data sheet	-	PDTB123E_SER_1
PDTB123E_SER_1	20050427	Product data sheet	-	-

PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PNP 500 mA resistor-equipped transistor; R1 = 2.2 k Ω , R2 = 2.2 k Ω

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